SYNSEMI SEMICONDUCTOR

RBV1000 - RBV1010

SILICON BRIDGE RECTIFIERS

PRV : 50 - 1000 Volts
Io : 10 Amperes

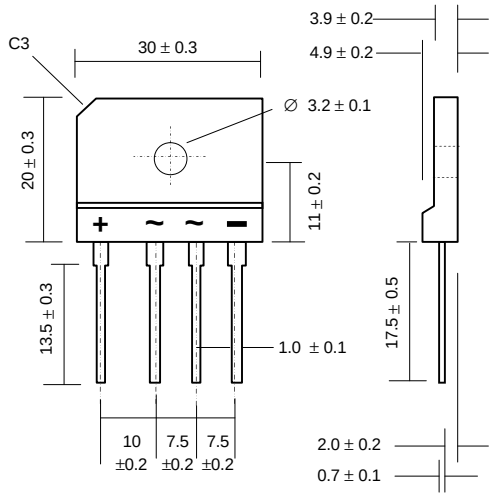
FEATURES :

* High current capability
* High surge current capability
* High reliability
* Low reverse current
* Low forward voltage drop
* High case dielectric strength of 2000 V_{DC}
* Ideal for printed circuit board
* Very good heat dissipation
* Pb / RoHS Free

MECHANICAL DATA :

* Case : Reliable low cost construction utilizing molded plastic technique
* Epoxy : UL94V-O rate flame retardant
* Terminals : Plated lead solderable per MIL-STD-202, Method 208 guaranteed
* Polarity : Polarity symbols marked on case
* Mounting position : Any
* Weight : 7.97 grams (Approximaly)

RBV25



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

RATING	SYMBOL	RBV 1000	RBV 1001	RBV 1002	RBV 1004	RBV 1006	RBV 1008	RBV 1010	UNIT
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Current Tc = 55°C	$I_{F(AV)}$	10							A
Peak Forward Surge Current Single half sine wave Superimposed on rated load (JEDEC Method)	I_{FSM}	300							A
Current Squared Time at t < 8.3 ms.	I^2t	160							A^2S
Maximum Forward Voltage per Diode at I_F = 5.0 A	V_F	1.0							V
Maximum DC Reverse Current Ta = 25 °C	I_R	10							µA
at Rated DC Blocking Voltage Ta = 100 °C	$I_{R(H)}$	200							µA
Typical Thermal Resistance (Note 1)	RθJC	2.5							°C/W
Operating Junction Temperature Range	T_J	- 40 to + 150							°C
Storage Temperature Range	T_{STG}	- 40 to + 150							°C

Notes :

1. Thermal Resistance from junction to case with units mounted on a 3.2" x 3.2" x 0.12" (8.2cm.x 8.2cm.x 0.3cm.) Al.-Finned Plate.

RATING AND CHARACTERISTIC CURVES (RBV1000 - RBV1010)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

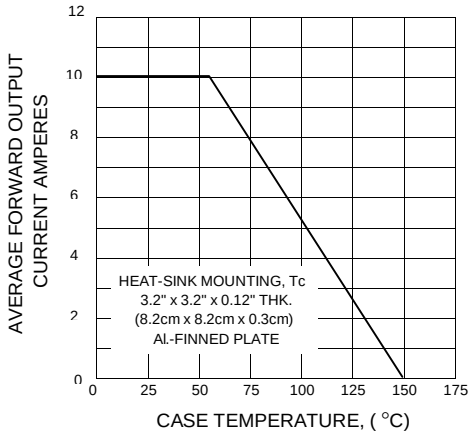


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

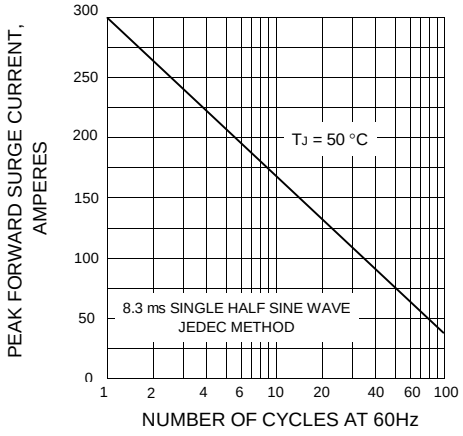


FIG.3 - TYPICAL FORWARD CHARACTERISTICS PER DIODE

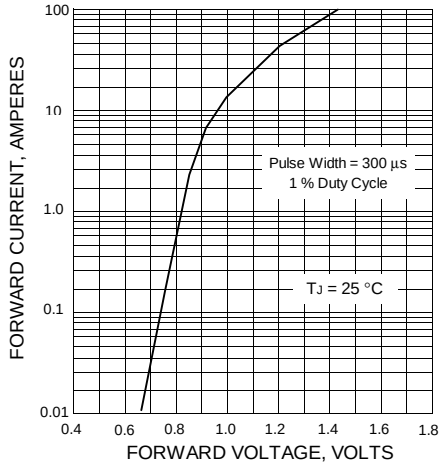


FIG.4 - TYPICAL REVERSE CHARACTERISTICS PER DIODE

